

Schottky Barrier Rectifiers

Using the Schottky Barrier principle with a Molybdenum barrier metal. These state-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes.

Features

- * Low Forward Voltage.
- * Low Switching noise.
- * High Current Capacity
- * Guarantee Reverse Avalanche.
- * Guard-Ring for Stress Protection.
- * Low Power Loss & High efficiency.
- * 150 Operating Junction Temperature
- * Low Stored Charge Majority Carrier Conduction.
- * Plastic Material used Carries Underwriters Laboratory Flammability Classification 94V-O



* In compliance with EU RoHs 2002/95/EC directives

MAXIMUM RATINGS

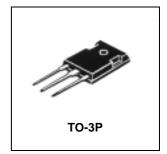
Characteristic	Symbol	S40D90C	S40D100C	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	90	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	63	70	V
Average Rectifier Forward Current (per diode) Total Device (Rated V _R),T _C =100	I _{F(AV)}	20 40		Α
Peak Repetitive Forward Current (Rate V _R , Square Wave, 20kHz)	I _{FM}	40		Α
Non-Repetitive Peak Surge Current (Surge applied at rate load conditions halfware, single phase, 60Hz)	I _{FSM}	300		А
Operating and Storage Junction Temperature Range	T_J , T_{STG}	-65 to +150		

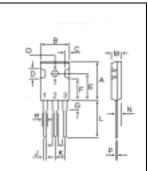
ELECTRIAL CHARACTERISTICS

Characteristic	Symbol	S40D90C	S40D100C	Unit
Maximum Instantaneous Forward Voltage ($I_F = 20 \text{ Amp } T_C = 25$) ($I_F = 20 \text{ Amp } T_C = 125$)	V _F	0.85 0.75		V
Maximum Instantaneous Reverse Current (Rated DC Voltage, $T_C = 25$) (Rated DC Voltage, $T_C = 125$)	I _R	1.0 80		mA

SCHOTTKY BARRIER RECTIFIERS

40 AMPERES 90-100 VOLTS





DIM	MILLIMETERS		
	MIN	MAX	
Α	20.63	22.38	
В	15.38	16.20	
С	1.90	2.70	
D	5.10	6.10	
Ε	14.81	15.22	
F	11.72	12.84	
G	4.20	4.50	
Н	1.82	2.46	
1	2.92	3.23	
J	0.89	1.53	
K	5.26	5.66	
L	18.50	21.50	
М	4.68	5.36	
N	2.40	2.80	
0	3.25	3.65	
Р	0.55	0.70	

